

Silicon N-Channel Planar Power MOSFET

Description

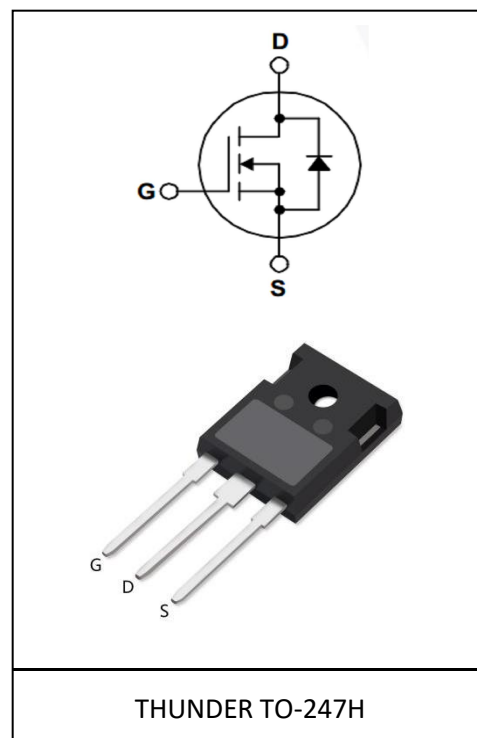
The TH70N20PKH utilizes the latest processing techniques to achieve low on-resistance per silicon area. Additional features of this MOSFET are 150°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for PDP driving applications. It can be used in a wide variety of applications.

General Features

- $V_{DS}=200V, I_D=70A$
- Low ON Resistance, $R_{DS(ON)}=28m\Omega @ V_{GS}=10V, I_D=35A$
- Low reverse transfer capacitance
- Low Qg for fast response
- Short fall & rise times for fast switching
- 100% single pulse avalanche energy Test

Application

- Power switching application
- Digital amplifier
- Adapter and charger



Product Summary

V_{DS}	200V
$R_{DS(on)}$	28m Ω
I_D	70A

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	200	V
Continuous drain current $T_C = 25^\circ C$ (Silicon limit)	I_D	70	A
Pulsed drain current ($T_C = 25^\circ C$, t_p limited by T_{jmax})	I_{DM}	280	A
Avalanche energy, single pulse ($L=10mH$, $R_g=25\Omega$)	E_{AS}	3047	mJ
Gate-Source voltage	V_{GS}	± 30	V
Power dissipation ($T_C = 25^\circ C$)	P_D	463	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ C$

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.27	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	40	

Electrical Characteristic (at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	200	-	-	V	$V_{GS}=0\text{ V}, I_D=250\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	2.0	-	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=200\text{ V}, V_{GS}=0\text{ V}$ $T_j=25\text{ }^{\circ}\text{C}$
		-	-	10	μA	$V_{DS}=160\text{ V}, V_{GS}=0\text{ V}$ $T_j=125\text{ }^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 30\text{ V}, V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	28	37	m Ω	$V_{GS}=10\text{ V}, I_D=35\text{ A}$
Transconductance	g_{fs}	-	47	-	S	$V_{DS}=40\text{ V}, I_D=35\text{ A}$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	5351	-	pF	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$
Output Capacitance	C_{oss}	-	609	-		
Reverse Transfer Capacitance	C_{rss}	-	14	-		
Gate Total Charge	Q_g	-	65	-	nC	$V_{GS}=10\text{ V}, V_{DS}=160\text{ V},$ $I_D=70\text{ A}$
Gate-Source charge	Q_{gs}	-	20	-		
Gate-Drain charge	Q_{gd}	-	25	-		
Turn-on delay time	$t_{d(on)}$	-	70	-	ns	$V_{DD}=100\text{ V}, I_D=70\text{ A},$ $R_G=25\text{ }\Omega$
Rise time	t_r	-	230	-		
Turn-off delay time	$t_{d(off)}$	-	66	-		
Fall time	t_f	-	38	-		
Gate resistance	R_G	-	0.29	-	Ω	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V},$ $f=1\text{ MHz}$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	-	1.5	V	$V_{GS}=0V, I_{DS}=70A$
Body Diode Continuous Forward Current	I_S	-	-	70	A	$T_C=25^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	180	-	ns	$T_C=25^{\circ}C, I_S=70A,$ $di/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	-	4.2	-	μC	

Typical Performance Characteristics

Fig 1: On-Region Characteristics

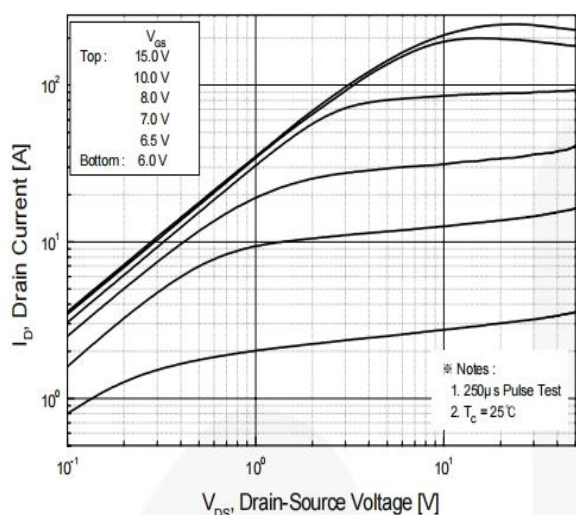


Fig 2: Transfer Characteristics

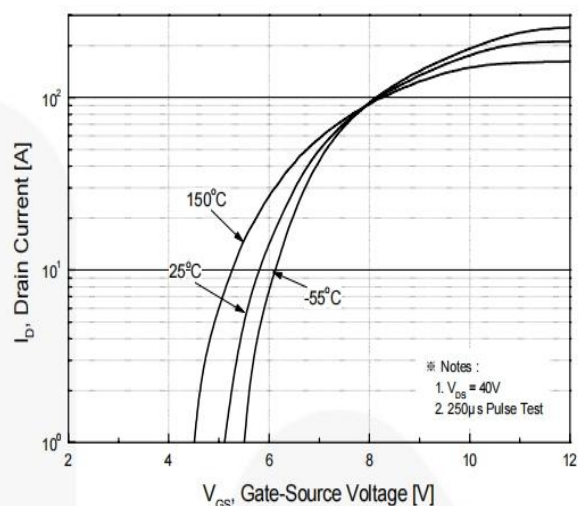


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

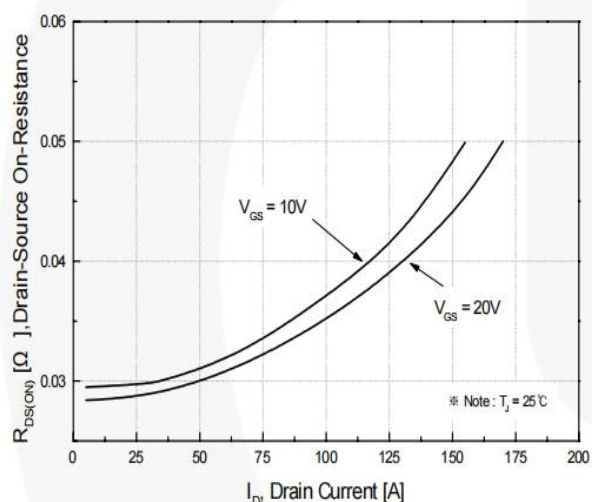


Fig 4: Body-Diode Forward Voltage Variation vs. Source Current and Temperature

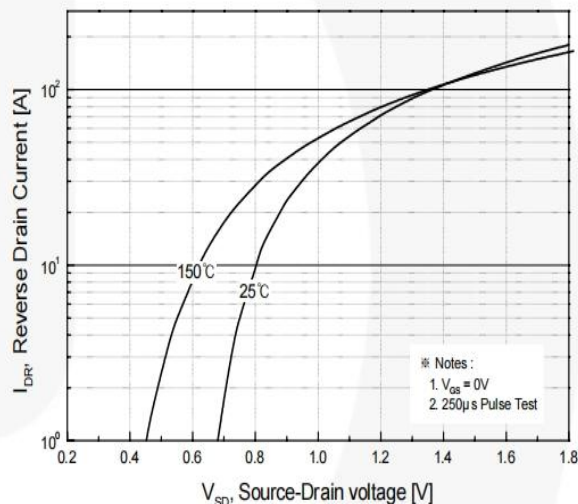


Fig 5: Gate Charge Characteristics

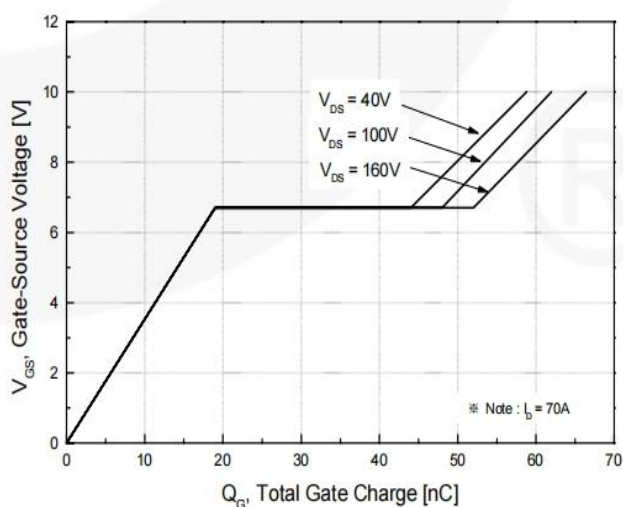


Fig 6: Capacitance Characteristics

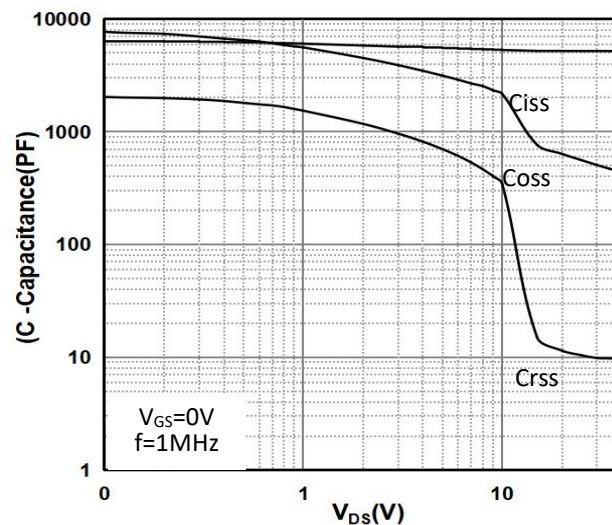


Fig 7: Power Dissipation

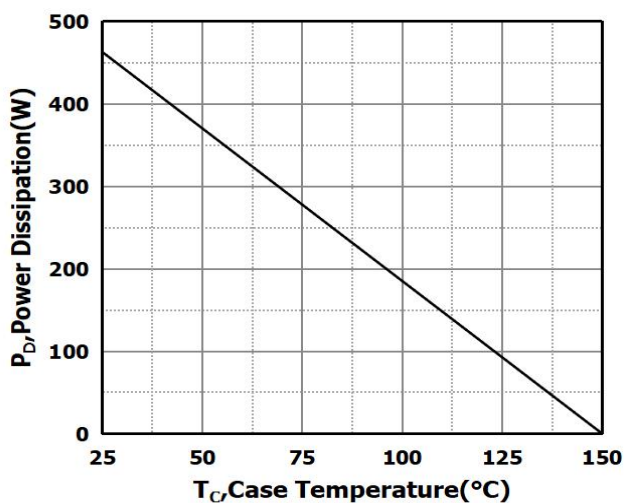


Fig 8: Drain Current Derating

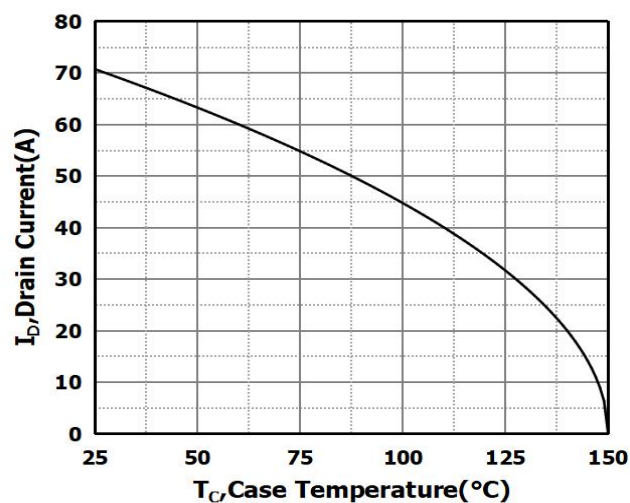


Fig 9: Rds(on) vs. Temperature

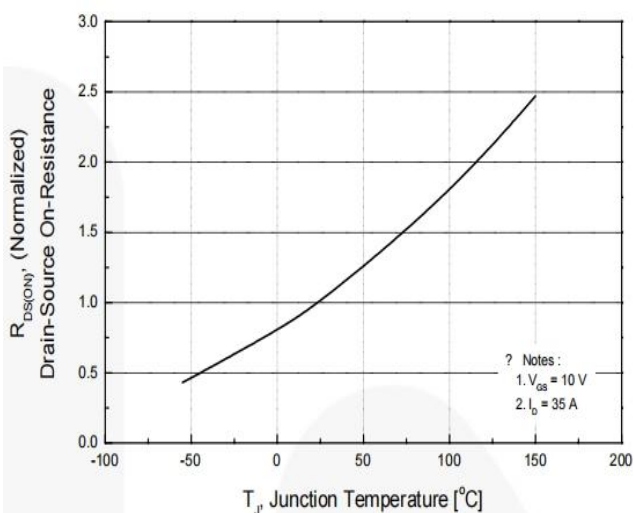


Fig 10: Breakdown Voltage Variation vs. Temperature

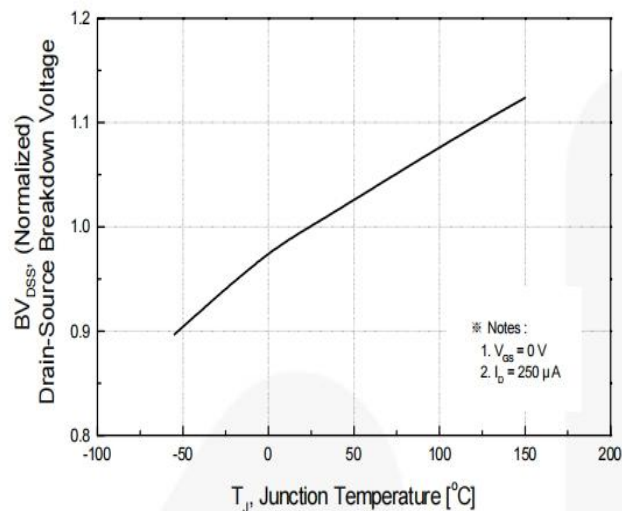


Fig 11: Safe Operating Area

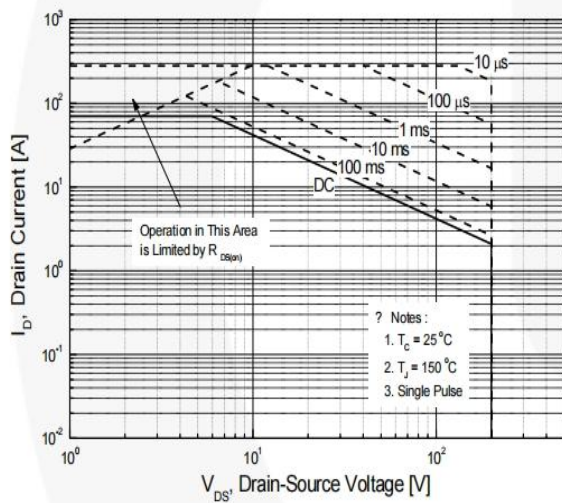
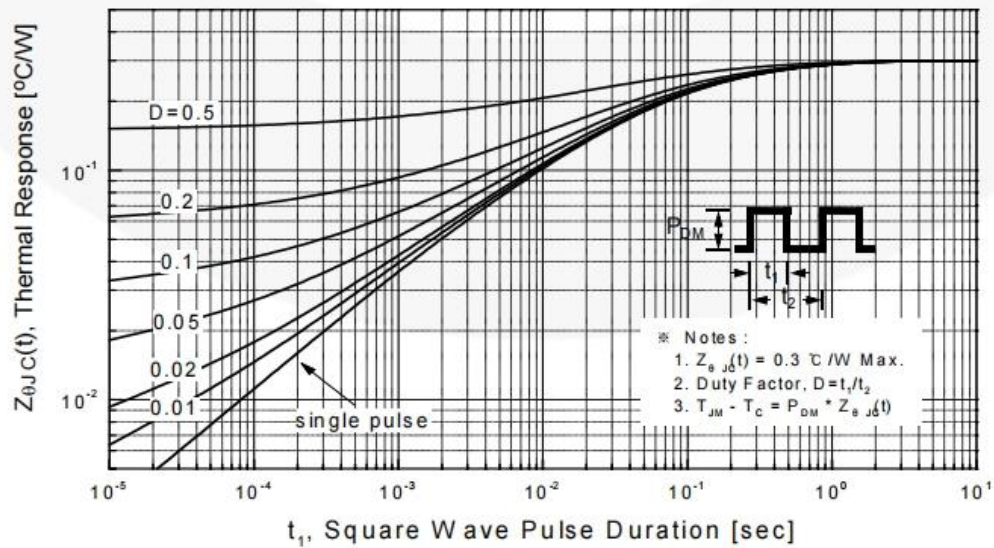
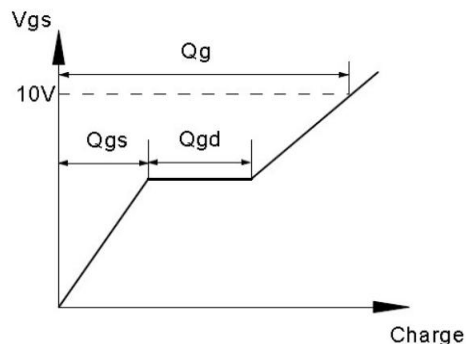
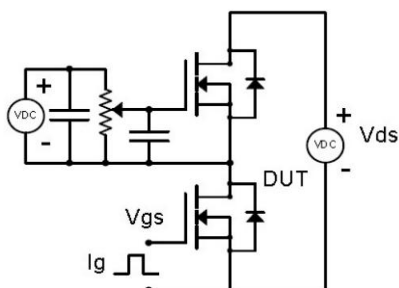


Fig 12: Maximum Effective Transient Thermal Impedance, Junction-to-Case

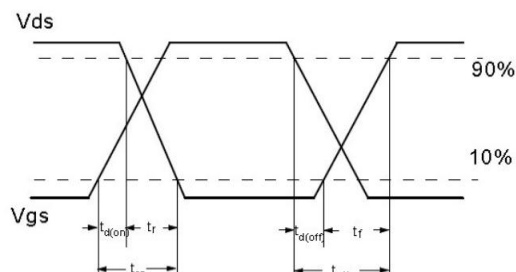
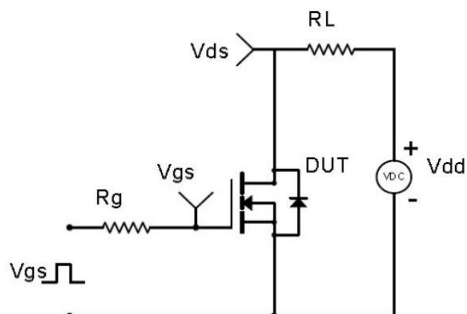


Test Circuit & Waveform

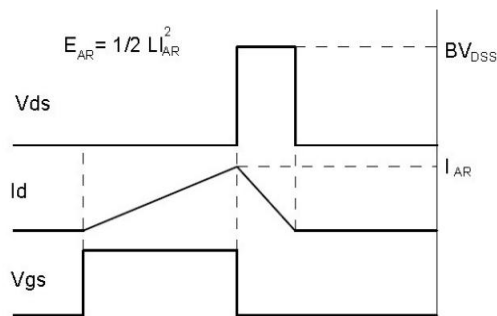
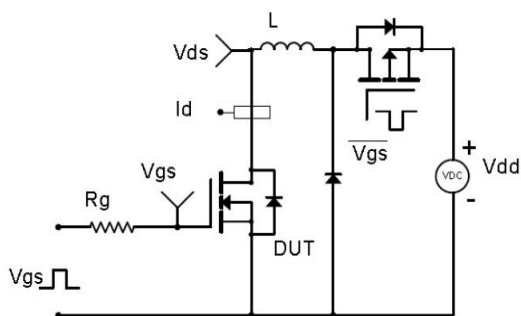
Gate Charge Test Circuit & Waveform



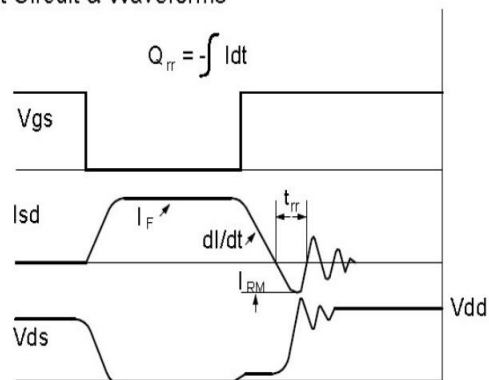
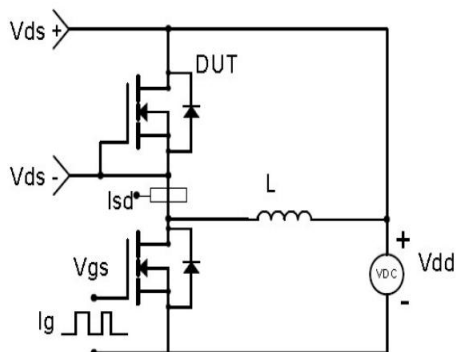
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



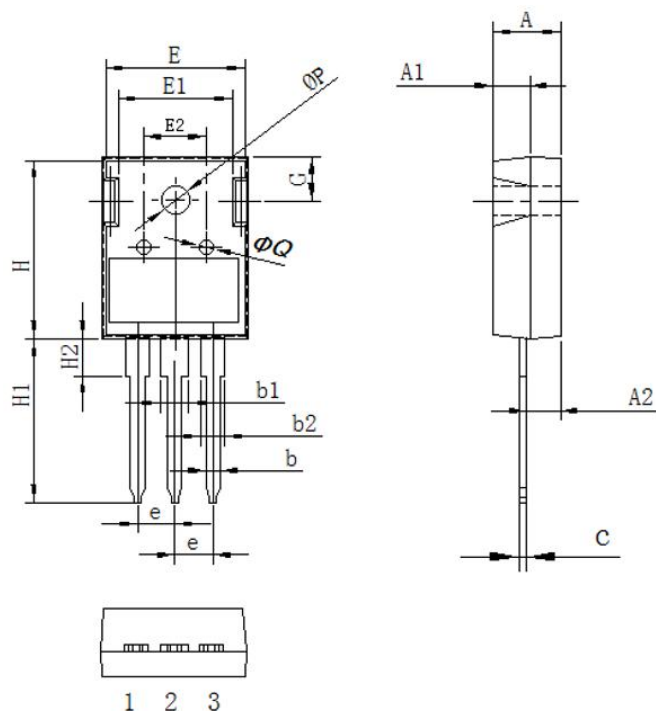
Diode Recovery Test Circuit & Waveforms



Package Information

TO-247H PACKAGE

基本尺寸



Symbol	单位 mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.80	3.00	3.20
A2	2.20	2.40	2.60
b	1.05	1.20	1.35
b1	2.80	3.00	3.20
b2	1.80	2.00	2.20
c	0.50	0.60	0.70
e	5.35	5.45	5.75
E	15.6	15.80	16.0
E1	12.3	12.50	12.7
E2	6.00	6.20	6.40
H	20.5	21.0	21.5
H1	19.0	20.0	21.0
H2	3.00	4.00	5.00
G	5.70	5.90	6.10
ΦP	3.30	3.50	3.50
ΦQ	2.30	2.50	2.70

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